



Description

JMG N-channel Enhancement Mode Power MOSFET

Features

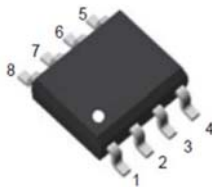
- 100V,7A
 $R_{DS(ON)} < 140m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 300m\Omega @ V_{GS} = 4.5V$
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

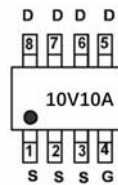
- Load Switch
- PWM Application
- Power management



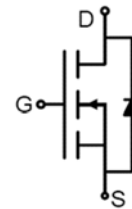
100% UIS TESTED!
100% ΔVds TESTED!



SOP-8 top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
10V10A	JMGP10V10A	TAPING	SOP-8	13inch	4000	48000

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V _{DSS}	Drain-Source Voltage	100	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	T _C = 25°C	7 A
		T _C = 100°C	4.5 A
I _{DM}	Pulsed Drain Current ^{note1}	28	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	2.25	mJ
P _D	Power Dissipation	T _C = 25°C	13.7 W
R _{θJC}	Thermal Resistance, Junction to Case	9.1	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	1.5	-	2.5	V
R _{DSON}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =10V, I _D =3.5A	-	110	140	mΩ
		V _{GS} =4.5V, I _D =2A	-	160	300	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f = 1MHz	-	206	-	pF
C _{oss}	Output Capacitance		-	29	-	pF
C _{rss}	Reverse Transfer Capacitance		-	1.4	-	pF
Q _g	Total Gate Charge	V _{DS} =25V, I _D =5A, V _{GS} =10V	-	4.3	-	nC
Q _{gs}	Gate-Source Charge		-	1.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.1	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =25V, I _D =5A, R _{GEN} =2Ω, V _{GS} =10V	-	14.7	-	ns
t _r	Turn-on Rise Time		-	3.5	-	ns
t _{d(off)}	Turn-off Delay Time		-	20.9	-	ns
t _f	Turn-off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	7	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	28	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =7A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =5A, di/dt=100A/μs	-	32	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	39	-	nC

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
 2. EAS condition: T_J=25°C, V_{DD}=50V, V_G=10V, R_G=50Ω, L=0.5mH, I_{AS}=3A
 3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

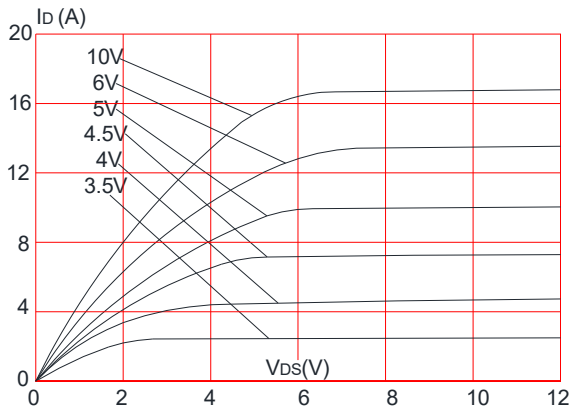


Figure 2: Typical Transfer Characteristics

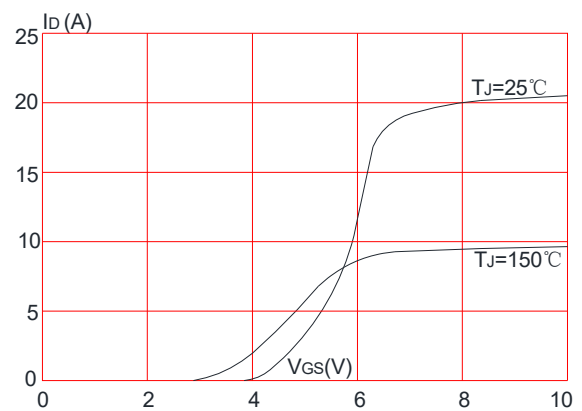


Figure 3: On-resistance vs. Drain Current

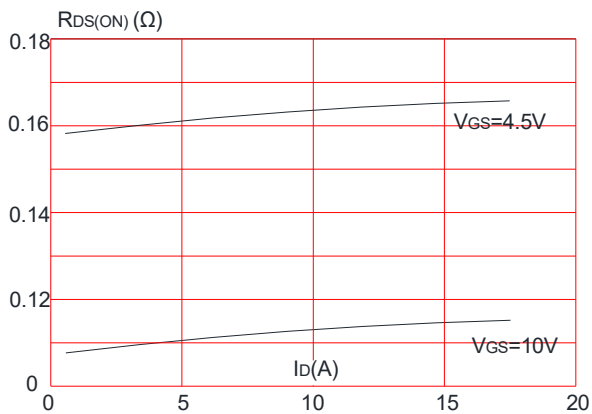


Figure 4: Body Diode Characteristics

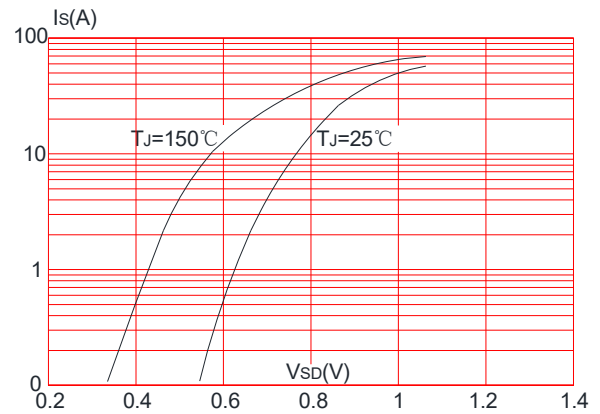


Figure 5: Gate Charge Characteristics

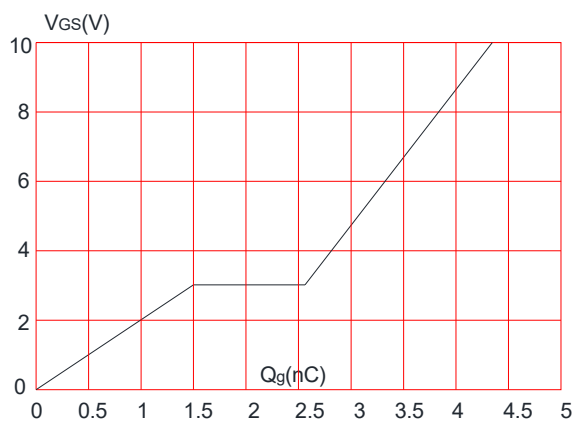


Figure 6: Capacitance Characteristics

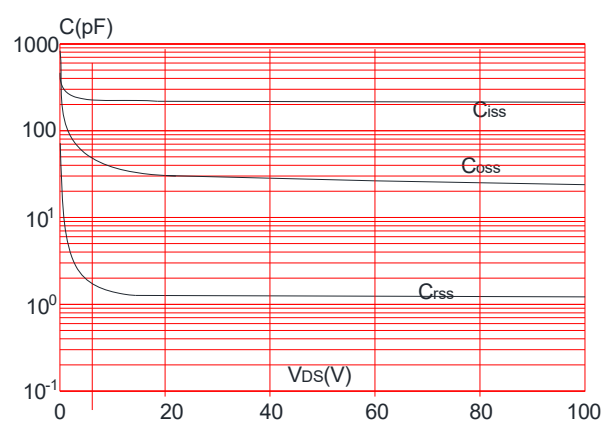




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

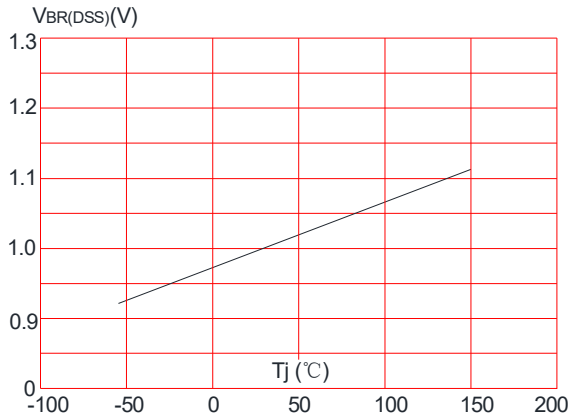


Figure 8: Normalized on Resistance vs. Junction Temperature

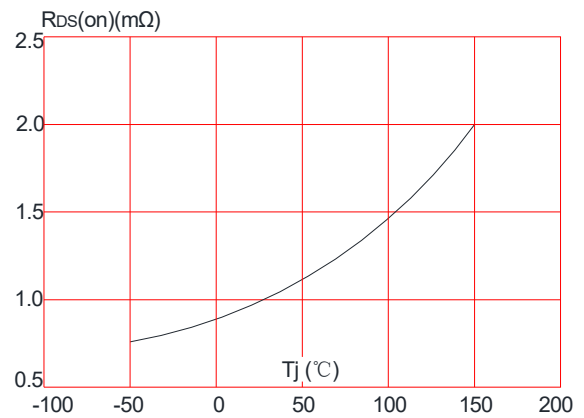


Figure 9: Maximum Safe Operating Area

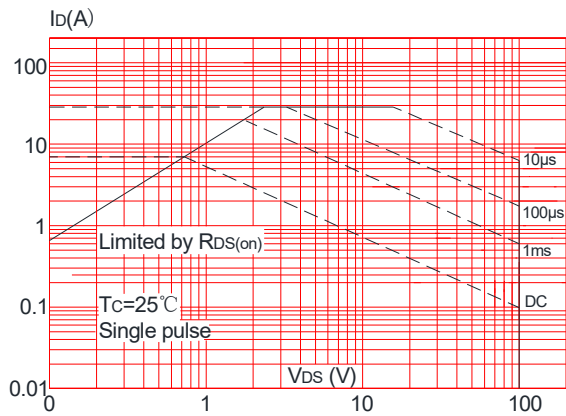


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

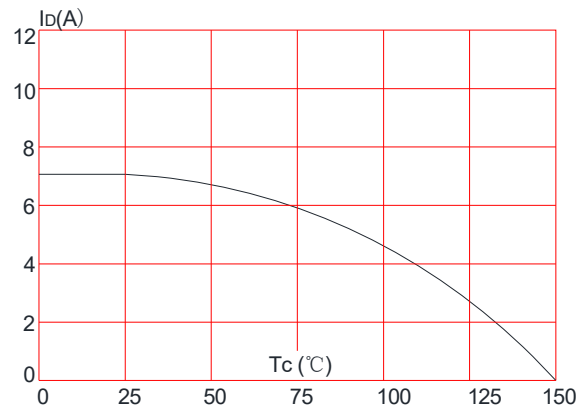
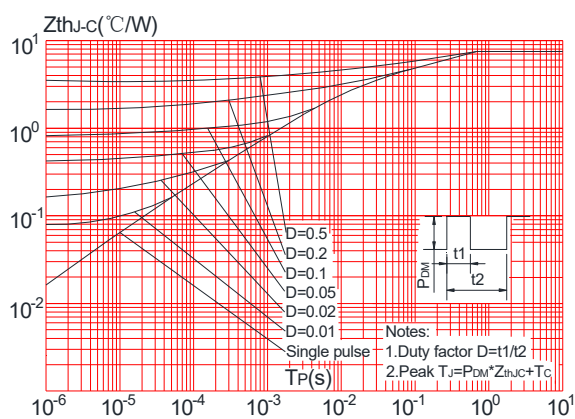


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

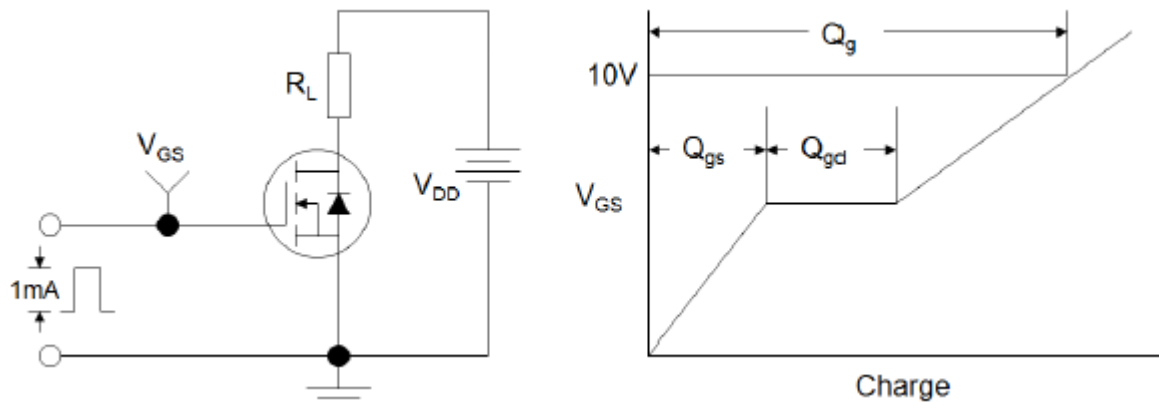


Figure1:Gate Charge Test Circuit & Waveform

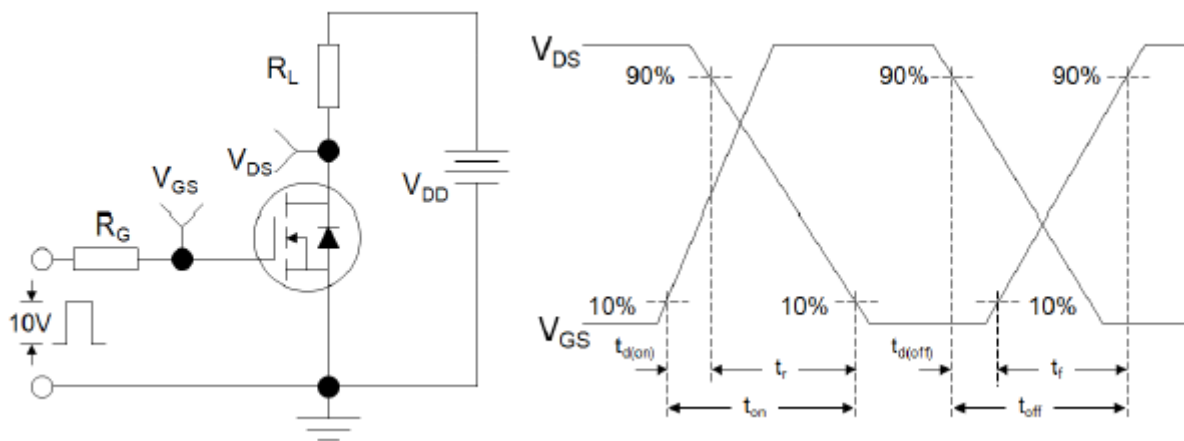


Figure 2: Resistive Switching Test Circuit & Waveforms

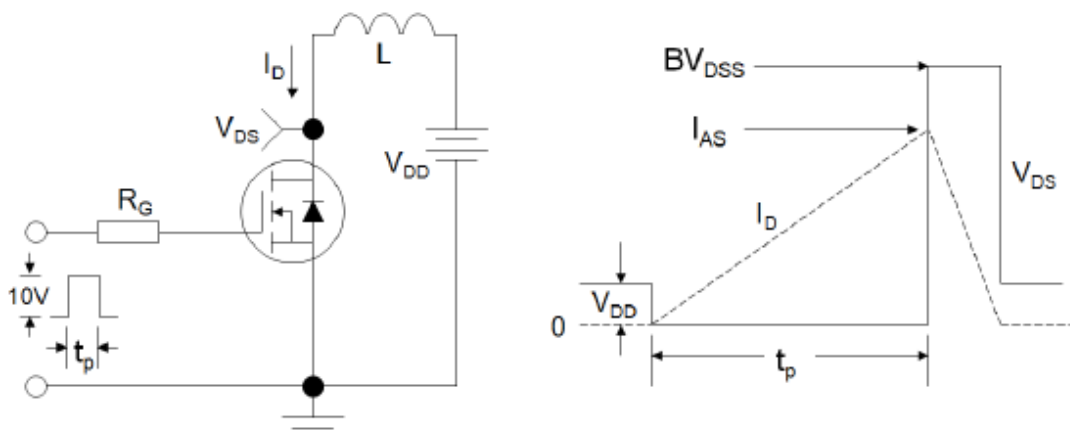
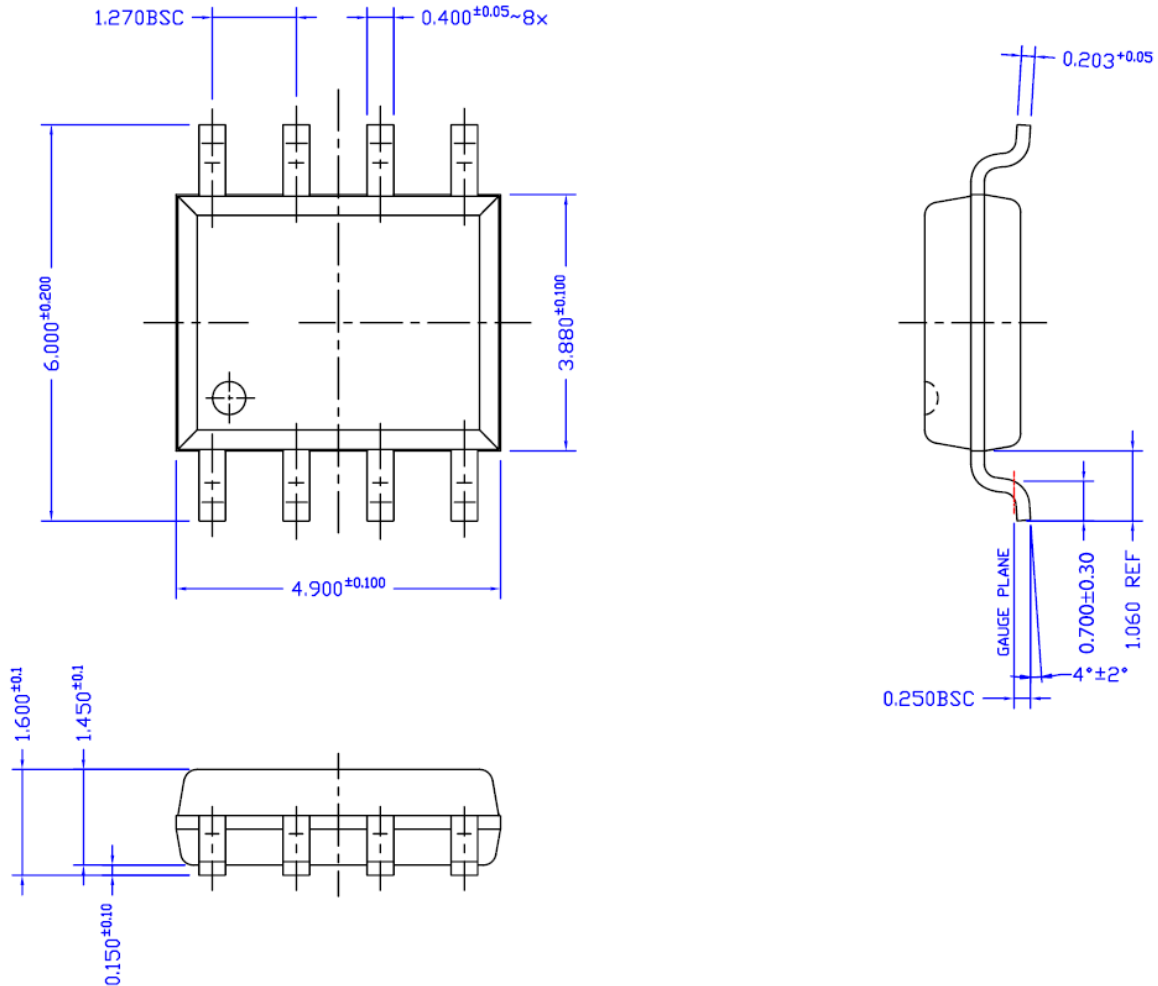


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Package Mechanical Data-SOP-8



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